



PTO/SB/08a/b (08-03)
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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Complete if Known		
			Application Number	10/602,720	
			Filing Date	June 25, 2003	
			First Named Inventor	John T. Moore	
			Art Unit	2811	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	3	Attorney Docket Number	M4065.0675/P675

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
HL	A	US 2004/0035401	2/2004	Ramachandran et al.	
	B	US 2003/0212724	11/2003	Ovshinsky et al.	
	C	US 2003/0048744	3/2003	Ovshinsky et al.	
	D	US 2003/0212725	11/2003	Ovshinsky et al.	
	E	US RE 37,259E	7/2001	Ovshinsky	
	F	US 3,271,591	9/1966	Ovshinsky	
	G	US 3,961,314	6/1976	Klose et al.	
	H	US 3,966,317	6/1976	Wacks et al.	
	I	US 3,983,542	11/1976	Ovshinsky	
	J	US 3,988,720	10/1976	Ovshinsky	
	K	US 4,177,474	12/1979	Ovshinsky	
	L	US 4,267,261	5/1981	Hallman et al.	
	M	US 4,597,162	7/1986	Johnson et al.	
	N	US 4,608,296	8/1986	Keem et al.	
	O	US 4,637,895	1/1987	Ovshinsky et al.	
	P	US 4,646,266	2/1987	Ovshinsky et al.	
	Q	US 4,664,939	5/1987	Ovshinsky	
	R	US 4,668,968	5/1987	Ovshinsky et al.	
	S	US 4,670,763	6/1987	Ovshinsky et al.	
	T	US 4,673,957	6/1987	Ovshinsky et al.	
	U	US 4,678,679	7/1987	Ovshinsky	
	V	US 4,696,758	9/1987	Ovshinsky et al.	
	W	US 4,698,234	10/1987	Ovshinsky et al.	
	X	US 4,710,899	12/1987	Young et al.	
	Y	US 4,728,406	3/1988	Banerjee et al.	
	Z	US 4,737,379	4/1988	Hudgens et al.	
	A1	US 4,766,471	8/1988	Ovshinsky et al.	
	B1	US 4,769,338	9/1988	Ovshinsky et al.	
	C1	US 4,775,425	10/1988	Guha et al.	
	D1	US 4,788,594	11/1988	Ovshinsky et al.	
	E1	US 4,809,044	2/1989	Pryor et al.	
	F1	US 4,818,717	4/1989	Johnson et al.	
	G1	US 4,843,443	6/1989	Ovshinsky et al.	
	H1	US 4,845,533	7/1989	Pryor et al.	
	I1	US 4,853,785	8/1989	Ovshinsky et al.	
	J1	US 4,891,330	1/1990	Guha et al.	
	K1	US 5,128,099	7/1992	Strand et al.	
	L1	US 5,159,661	10/1992	Ovshinsky et al.	
	M1	US 5,166,758	11/1992	Ovshinsky et al.	
	N1	US 5,177,567	1/1993	Klersy et al.	
	O1	US 5,296,716	3/1994	Ovshinsky et al.	
	P1	US 5,335,219	8/1994	Ovshinsky et al.	
	Q1	US 5,359,205	10/1994	Ovshinsky	
	R1	US 5,341,328	8/1994	Ovshinsky et al.	
LM	S1	US 5,406,509	4/1995	Ovshinsky et al.	

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T1	US 5,414,271	5/1995	Ovshinsky et al.	
U1	US 5,534,711	7/1996	Ovshinsky et al.	
V1	US 5,534,712	7/1996	Ovshinsky et al.	
W1	US 5,536,947	7/1996	Klersy et al.	
X1	US 5,543,737	8/1996	Ovshinsky	
Y1	US 5,591,501	1/1997	Ovshinsky et al.	
Z1	US 5,596,522	1/1997	Ovshinsky et al.	
A2	US 5,687,112	11/1997	Ovshinsky	
B2	US 5,694,054	12/1997	Ovshinsky et al.	
C2	US 5,714,768	2/1998	Ovshinsky et al.	
D2	US 5,825,046	10/1998	Czubatyj et al.	
E2	US 5,912,839	6/1999	Ovshinsky et al.	
F2	US 5,933,365	8/1999	Klersy et al.	
G2	US 6,011,757	1/2000	Ovshinsky	
H2	US 6,087,674	7/2000	Ovshinsky et al.	
I2	US 6,141,241	10/2000	Ovshinsky et al.	
J2	US 6,339,544	1/2002	Chiang et al.	
K2	US 6,404,665	6/2002	Lowery et al.	
L2	US 6,429,064	8/2002	Wicker	
M2	US 6,437,383	8/2002	Xu	
N2	US 6,462,984	10/2002	Xu et al.	
O2	US 6,480,438	11/2002	Park	
P2	US 6,487,113	11/2002	Park et al.	
Q2	US 6,501,111	12/2002	Lowery	
R2	US 6,507,061	1/2003	Hudgens et al.	
S2	US 6,511,862	1/2003	Hudgens et al.	
T2	US 6,511,867	1/2003	Lowery et al.	
U2	US 6,512,241	1/2003	Lai	
V2	US 6,514,805	2/2003	Xu et al.	
W2	US 6,531,373	3/2003	Gill et al.	
X2	US 6,534,781	3/2003	Dennison	
Y2	US 6,545,287	4/2003	Chiang	
Z2	US 6,545,907	4/2003	Lowery et al.	
A3	US 6,555,860	4/2003	Lowery et al.	
B3	US 6,563,164	5/2003	Lowery et al.	
C3	US 6,566,700	5/2003	Xu	
D3	US 6,567,293	5/2003	Lowery et al.	
E3	US 6,569,705	5/2003	Chiang et al.	
F3	US 6,570,784	5/2003	Lowery	
G3	US 6,576,921	6/2003	Lowery	
H3	US 6,586,761	7/2003	Lowery	
I3	US 6,589,714	7/2003	Maimon et al.	
J3	US 6,590,807	7/2003	Lowery	
K3	US 6,593,176	7/2003	Dennison	
L3	US 6,597,009	7/2003	Wicker	
M3	US 6,605,527	8/2003	Dennison et al.	
N3	US 6,613,604	9/2003	Maimon et al.	
O3	US 6,621,095	9/2003	Chiang et al.	
P3	US 6,625,054	9/2003	Lowery et al.	
Q3	US 6,642,102	11/2003	Xu	

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U1	R3	US 6,646,297	11/2003	Dennison	
	S3	US 6,649,928	11/2003	Dennison	
	T3	US 6,667,900	12/2003	Lowery et al.	
	U3	US 6,671,710	12/2003	Ovshinsky et al.	
	V3	US 6,673,648	1/2004	Lowrey	
	W3	US 6,673,700	1/2004	Dennison et al.	
	X3	US 6,674,115	1/2004	Hudgens et al.	
	Y3	US 6,687,427	2/2004	Ramalingam et al.	
	Z3	US 6,690,026	2/2004	Peterson	
	A4	US 6,696,355	2/2004	Dennison	
	B4	US 6,687,153	2/2004	Lowery	
	C4	US 6,707,712	3/2004	Lowery	
U1	D4	US 6,714,954	3/2004	Ovshinsky et al.	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁵
		Country Code ² -Number ³ -Kind Code ⁴ (if known)					

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NON PATENT LITERATURE DOCUMENTS				
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				T ²

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¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	Huan Hoang	Date Considered	8/18/04
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			Filing Date	June 25, 2003	
			First Named Inventor	John T. Moore	
			Art Unit	2811	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	1	Attorney Docket Number	M4065.0675/P675

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		Number-Kind Code ² (if known)			

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
HH	AA	KAWAMOTO, Yoji And NISHIDA, Masaru, IONIC CONDUCTION IN As ₂ S ₃ —Ag ₂ S, GeS ₂ —GeS—Ag ₂ S AND P ₂ S ₅ —Ag ₂ S GLASSES, Journal of Non-Crystalline Solids 20 (1976) 393-404.	

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Huan Hoang

8/18/04



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PTO/SB/08A (10-01)

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U. S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

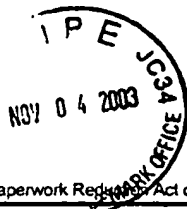
Complete If Known

Application Number	10/602,720
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First Named Inventor	John T. Moore
Art Unit	N/A
Examiner Name	N/A
Attorney Docket Number	M4065.0675/P675

Sheet 1 of 11

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Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
HK	AA	2002/0000666	1/3/2002	Kozicki et al.	
	AB	2002/0072188	6/13/2002	Gilton	
	AC	2002/0106849	08/08/2002	Moore	
	AD	2002/0123169	9/2002	Moore et al.	
	AE	2002/0123248	9/2002	Moore et al.	
	AF	2002/0160551	10/31/2002	Harshfield	
	AG	2002/0163828	11/07/2002	Krieger et al.	
	AH	2002/0168820	11/2002	Kozicki	
	AI	2002/0123169	09/05/2002	Moore et al.	
	AJ	2002/0123170	09/05/2002	Moore et al.	
	AK	2002/0123248	09/05/2002	Moore et al.	
	AL	2002/0127886	09/12/2002	Moore et al.	
	AM	2002/0132417	09/09/2002	Li	
	AN	2002/0168852	11/14/2002	Harshfield et al.	
	AO	2002/0190289	12/19/2002	Harshfield et al.	
	AP	2002/0190350	12/19/2002	Kozicki et al.	
	AQ	2003/0001229	01/02/2003	Moore et al.	
	AR	2003/0027416	02/06/2003	Moore	
	AS	2003/0032254	02/13/2003	Gilton	
	AT	2003/0035314	02/20/2003	Kozicki	
	AU	2003/0035315	02/20/2003	Kozicki	
	AV	2003/0038301	02/27/2003	Moore	
	AW	2003/0043631	03/06/2003	Gilton et al.	
	AX	2003/0045049	03/06/2003	Campbell et al.	
	AY	2003/0045054	03/06/2003	Campbell et al.	
	AZ	2003/0047765	03/13/2003	Campbell	
	AA1	2003/0047772	03/13/2003	Li	
	AB1	2003/0047773	03/13/2003	Li	
	AC1	2003/0048519	03/13/2003	Kozicki	
	AD1	2003/0049912	03/13/2003	Campbell et al.	
	AE1	2003/0068861	04/10/2003	Li	
	AF1	2003/0068862	04/10/2003	Li	
	AG1	2003/0095426	05/22/2003	Hush et al.	
	AH1	2003/0096497	05/22/2003	Moore et al.	
	AI1	2003/0107105	06/12/2003	Kozicki	
	AJ1	2003/0117831	06/26/2003	Hush	
	AK1	2003/0128612	07/10/2003	Moore et al.	
	AL1	2003/0137869	07/24/2003	Kozicki	
	AM1	2003/0143782	07/31/2003	Gilton et al.	
	AN1	2003/1055589	08/21/2003	Campbell et al.	
	AO1	2003/0155606	08/21/2003	Campbell et al.	
	AP1	2003/0156447	08/21/2003	Kozicki	
	AQ1	2003/0156463	08/21/2003	Casper et al.	
HK	AR1	3,622,319	11/1971	Sharp	



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			Examiner Name	N/A	
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AS1	3,743,847	7/1973	Boland
AT1	4,269,935	5/1981	Masters et al.
AU1	4,312,938	1/1982	Drexler, et al.
AV1	4,316,946	1/1982	Masters, et al.
AW1	4,320,191	3/1982	Yoshikawa et al.
AX1	4,405,710	9/1983	Balasubramanyam et al.
AY1	4,419,421	12/1983	Wichelhaus, et al.
AZ1	4,499,557	2/1985	Holmberg et al.
AA2	4,671,618	06/09/1987	Wu et al.
AB2	4,795,657	1/1989	Formigoni et al.
AC2	4,800,526	01/24/1989	Lewis
AD2	4,847,674	7/1989	Sliwa et al.
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AF2	5,219,788	6/1993	Abernathy et al.
AG2	5,238,862	8/1993	Blalock et al.
AH2	5,272,359	12/21/1993	Nagasubramanian et al.
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AL2	5,360,981	11/1994	Owen et al.
AM2	5,500,532	3/19/1996	Kozicki et al.
AN2	5,512,328	4/1996	Yoshimura et al.
AO2	5,512,773	4/1996	Wolf et al.
AP2	5,726,083	3/1998	Takaishi
AQ2	5,751,012	5/12/1998	Wolstenholme et al.
AR2	5,761,115	6/1998	Kozicki et al.
AS2	5,789,277	8/1998	Zahorik et al.
AT2	5,814,527	9/29/1998	Wolstenholme et al
AU2	5,818,749	10/06/1998	Harshfield
AV2	5,841,150	11/1998	Gonzalez et al.
AW2	5,846,889	12/1998	Harbison et al.
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AY2	5,869,843	2/9/1999	Harshfield
AZ2	5,896,312	4/20/1999	Kozicki et al.
AA3	5,914,893	6/22/1999	Kozicki et al.
AB3	5,920,788	7/1999	Reinberg
AC3	5,998,066	12/1999	Block et al.
AD3	6,031,287	2/29/2000	Harshfield
AE3	6,072,716	06/06/2000	Jacobson et al.
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AJ3	6,143,604	11/2000	Chiang et al.
AK3	6,236,059	5/2001	Wolsteinholme et al.
AL3	6,297,170	10/2001	Gabriel et al.
AM3	6,300,684	10/2001	Gonzalez et al.
AN3	6,316,784	11/2001	Zahorik et al.
AO3	6,329,606	12/2001	Freyman et al.



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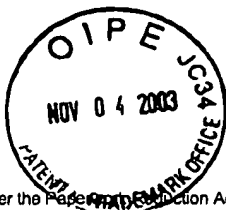
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AR3	6,376,284	4/2002	Gonzalez et al.	
AS3	6,388,324	5/14/2002	Kozicki et al.	
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AZ3	6,469,364	10/2002	Kozicki	
AA4	6,473,332	10/2002	Ignatiev et al.	
AB4	6,487,106	11/26/2002	Kozicki	
AC4	6,635,914	10/21/2003	Kozicki	

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		Country Code ² -Number ³ -Kind Code ⁴ (if known)					
HK	BA	56126916		10/19981	Akira et al.		
	BB	WO 97/48032		12/18/1997	Kozicki et al.		
	BC	WO 99/28914		06/10/1999	Kozicki et al.		
	BD	WO 00/48196		08/17/2000	Kozicki et al.		
HK	BE	WO 02/21542		03/14/2002	Kozicki et al.		

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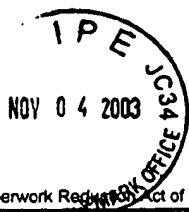


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			Application Number	10/602,720	
			Filing Date	June 25, 2003	
			First Named Inventor	John T. Moore	
			Group Art Unit	N/A	
			Examiner Name	N/A	
Sheet	4	of	11	Attorney Docket Number	M4065.0675/P675

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
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		Examiner Name	N/A
Sheet	5	of	11
		Attorney Docket Number	M4065.0675/P675

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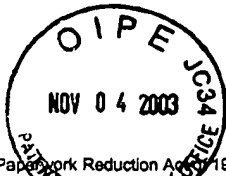


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			Group Art Unit	N/A	
			Examiner Name	N/A	
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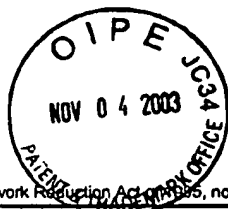
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		Group Art Unit	N/A
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